



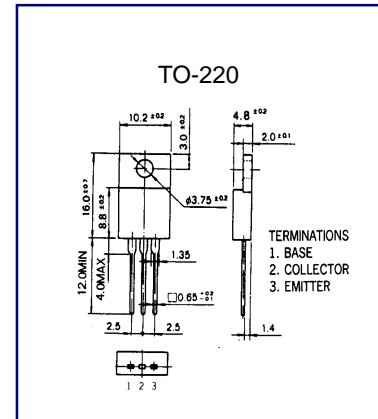
**2SC2233**

**NPN EPITAXIAL SILICON TRANSISTOR**

**LOW FREQUENCY POWER AMPLIFIER**

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	200	V
Collector-Emitter Voltage	V <sub>CE0</sub>	60	V
Emitter-Base voltage	V <sub>EB0</sub>	7	V
Collector Current (DC)	I <sub>C</sub>	4	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	40	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = 200V , I <sub>E</sub> =0			100	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 7V , I <sub>C</sub> =0			100	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> =1A	30		150	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =3A , I <sub>B</sub> =0.3A			1.0	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> =0.5A		8		MHZ

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.